



RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for digital and analog cellular PCN and PCS base station applications with frequencies from 1000 to 2500 MHz. Characterized for operation Class A and Class AB at 26 volts in commercial and industrial applications.


- Specified Two-Tone Performance @ 1930 and 2000 MHz, 26 Volts
 Output Power — 4 Watts PEP
 Power Gain — 11 dB
 Efficiency — 30%
 Intermodulation Distortion — -29 dBc
- Capable of Handling 10:1 VSWR, @ 26 Vdc,
 2000 MHz, 4 Watts CW Output Power

Features


- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- S-Parameter Characterization at High Bias Levels
- RoHS Compliant
- Available in Tape and Reel. R1 Suffix = 500 Units per 12 mm, 7 inch Reel.

MRF281SR1
MRF281ZR1

2000 MHz, 4 W, 26 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 458B-03, STYLE 1
NI-200S
MRF281SR1



CASE 458C-03, STYLE 1
NI-200Z
MRF281ZR1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	20 0.115	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5.74	$^\circ\text{C}/\text{W}$

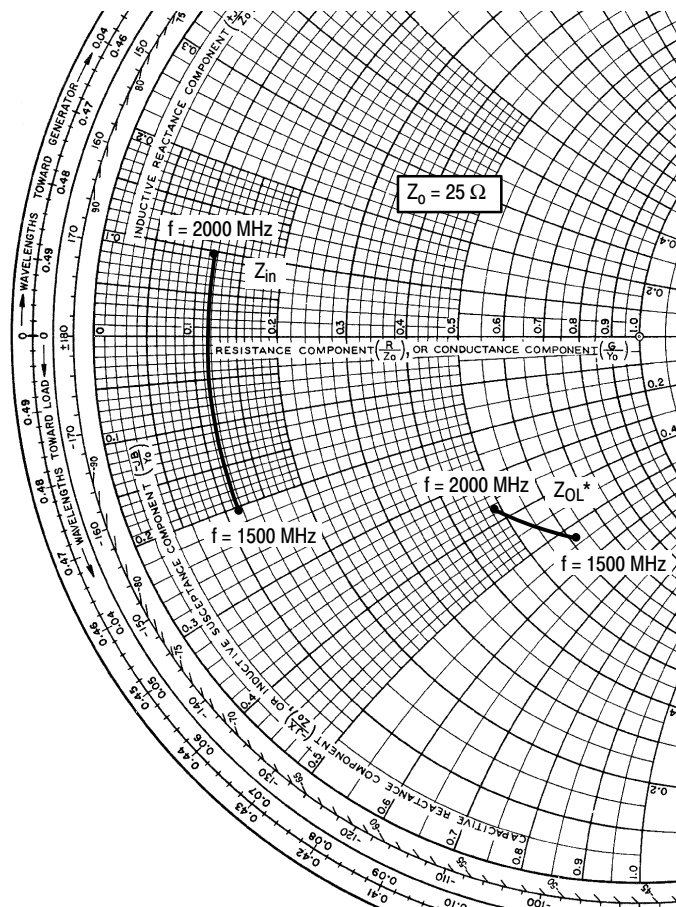
Table 3. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10 \mu\text{A}_{dc}$)	$V_{(BR)DSS}$	65	74	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 28 \text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	—	—	10	μA_{dc}
Gate-Source Leakage Current ($V_{GS} = 20 \text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	—	—	1	μA_{dc}

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 3. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 20\ \mu\text{Adc}$)	$V_{GS(th)}$	2.4	3.2	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 25\text{ mAdc}$)	$V_{GS(q)}$	3	4.1	5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 0.1\text{ A}$)	$V_{DS(on)}$	0.18	0.24	0.30	Vdc
Dynamic Characteristics					
Input Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{iss}	—	5.5	—	pF
Output Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{oss}	—	3.3	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{rss}	—	0.17	—	pF
Functional Tests (In Freescale Test Fixture)					
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	G_{ps}	11	12.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	η	30	33	—	%
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	IRL	—	-16	-10	dB
Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	IMD	—	-31	-29	dBc
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	G_{ps}	11	12.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	η	30	—	—	%
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	IRL	—	-16	-10	dB
Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	IMD	—	-31	—	dBc
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W CW}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$)	G_{ps}	10.5	12	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W CW}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$)	η	40	44	—	%



$V_{DD} = 26 \text{ V}$, $I_{DQ} = 25 \text{ mA}$, $P_{out} = 4 \text{ W (PEP)}$

f MHz	Z_{in} Ω	Z_{OL}^* Ω
1500	$3.15 - j5.3$	$15.5 - j13.6$
1600	$3.1 - j3.8$	$14.7 - j12.5$
1700	$3.1 - j2.3$	$14.0 - j11.7$
1800	$3.1 - j0.7$	$13.4 - j11.0$
1900	$3.1 + j0.9$	$12.8 - j10.1$
2000	$3.1 + j2.4$	$12.2 - j9.2$

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the optimum load impedance at given output power, voltage, IMD, bias current and frequency.

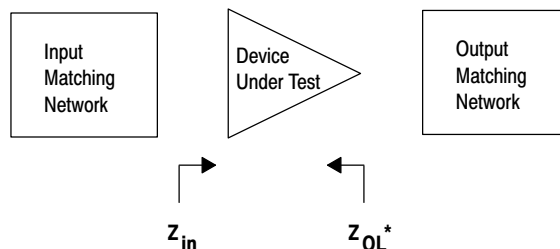


Figure 1. Series Equivalent Input and Output Impedance

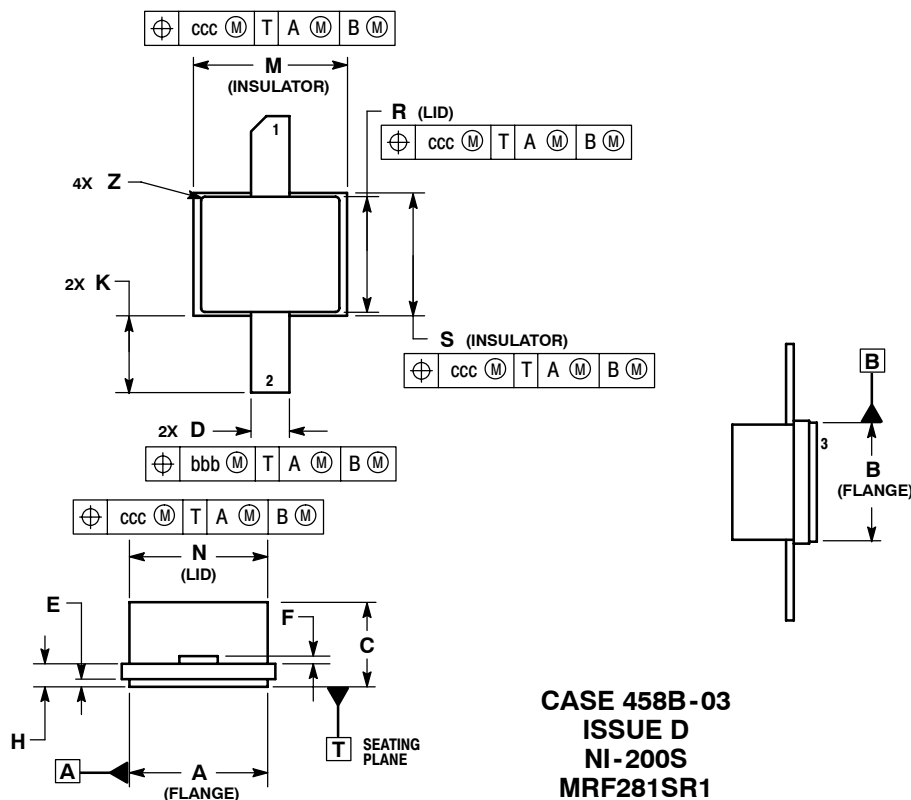
Table 4. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 250$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	dB	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.1	.982	-28	18.9	160	.008	73	.851	-13
0.2	.947	-52	17.0	143	.015	58	.811	-25
0.3	.912	-73	15.0	129	.019	45	.770	-33
0.4	.886	-90	12.9	117	.022	36	.741	-42
0.5	.859	-103	11.1	108	.022	28	.719	-47
0.6	.854	-114	9.69	100	.023	23	.718	-51
0.7	.841	-123	8.54	93	.022	18	.709	-56
0.8	.837	-131	7.57	87	.021	15	.714	-59
0.9	.838	-138	6.69	81	.019	12	.719	-62
1.0	.841	-143	6.01	76	.018	11	.728	-64
1.1	.840	-149	5.41	72	.015	12	.742	-66
1.2	.849	-153	4.91	68	.013	13	.745	-68
1.3	.848	-158	4.51	64	.012	18	.758	-69
1.4	.856	-162	4.12	60	.010	26	.769	-70
1.5	.858	-167	3.78	57	.009	36	.786	-70
1.6	.871	-170	3.50	54	.008	54	.797	-72
1.7	.868	-173	3.22	51	.009	69	.808	-71
1.8	.870	-176	3.00	49	.009	82	.823	-72
1.9	.872	-180	2.80	46	.011	95	.828	-72
2.0	.877	178	2.63	44	.013	104	.845	-72
2.1	.876	174	2.47	41	.015	109	.843	-72
2.2	.880	171	2.36	39	.018	111	.859	-71
2.3	.882	168	2.21	36	.021	114	.858	-72
2.4	.886	165	2.12	34	.024	114	.872	-70
2.5	.896	162	1.97	32	.027	115	.863	-70
2.6	.897	158	1.89	29	.029	117	.873	-69

NOTES

NOTES

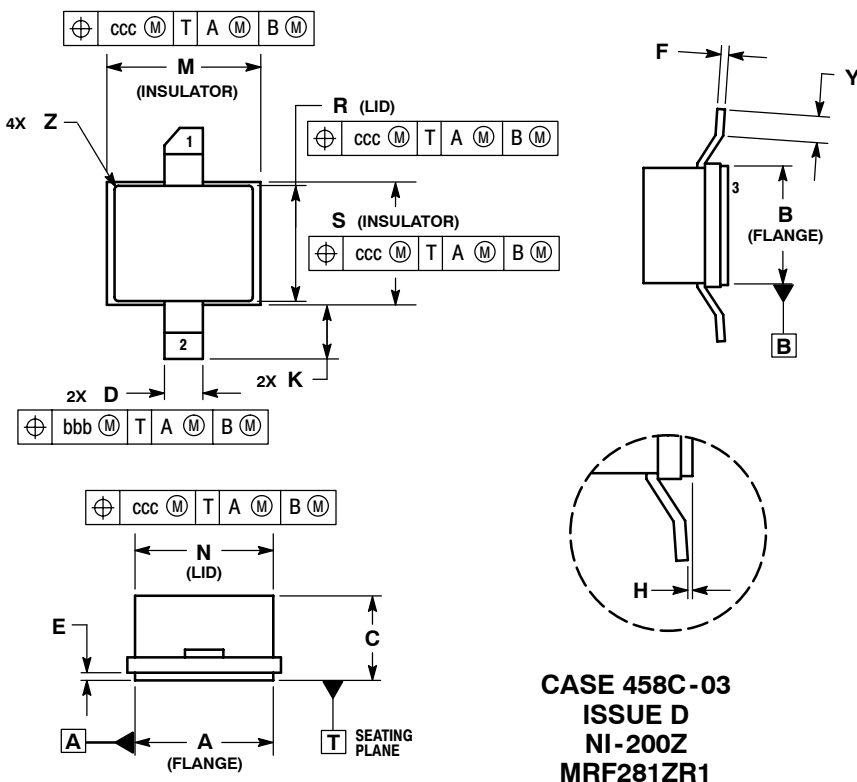
PACKAGE DIMENSIONS



- NOTES:
1. CONTROLLING DIMENSIONS: INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. ALL DIMENSIONS ARE SYMMETRICAL ABOUT CENTERLINE UNLESS OTHERWISE NOTED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.180	0.190	4.572	4.83
B	0.140	0.150	3.556	3.81
C	0.082	0.116	2.083	2.946
D	0.047	0.053	1.194	1.346
E	0.004	0.010	0.102	0.254
F	0.004	0.006	0.102	0.152
H	0.025	0.031	0.635	0.787
K	0.060	0.110	1.524	2.794
M	0.197	0.203	5.004	5.156
N	0.177	0.183	4.496	4.648
R	0.147	0.153	3.734	3.886
S	0.157	0.163	3.988	4.14
Z	---	0.020	---	0.508
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



- NOTES:
1. CONTROLLING DIMENSIONS: INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSION H (PACKAGE COPLANARITY): THE BOTTOM OF LEADS AND REFERENCE PLANE T MUST BE COPLANAR WITHIN DIMENSION H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.180	0.190	4.572	4.830
B	0.140	0.150	3.556	3.810
C	0.082	0.116	2.083	2.946
D	0.047	0.053	1.194	1.346
E	0.004	0.010	0.102	0.254
F	0.004	0.006	0.102	0.152
H	0.000	0.004	0.000	0.102
K	0.050	0.090	1.270	2.286
M	0.197	0.203	5.004	5.156
N	0.177	0.183	4.496	4.648
R	0.147	0.153	3.734	3.886
S	0.157	0.163	3.988	4.140
Y	0.020	0.040	0.508	1.016
Z	---	R.020	---	R.508
bbb	.010 REF		0.254 REF	
ccc	.015 REF		0.381 REF	

- STYLE 1:
PIN 1. DRAIN
2. GATE
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How to Reach Us:

Home Page:

www.freescale.com

E-mail:

support@freescale.com

USA/Europe or Locations Not Listed:

Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
Chandler, Arizona 85224
+1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:

Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:

Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
support.asia@freescale.com

For Literature Requests Only:

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